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March 2016

FQB34P10

P-Channel QFET® MOSFET

100 V, -33.5 A, 60 m Ω

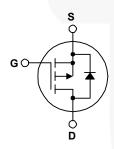
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- -33.5 A, -100 V, $R_{DS(on)}$ = 60 m Ω (Max.) @ V_{GS} = .10 V, I_{D} = -16.75 A
- Low Gate Charge (Typ. 85 nC)
- Low Crss (Typ. 170 pF)
- 100% Avalanche Tested
- · 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQB34P10TM	Unit
V_{DSS}	Drain-Source Voltage		-100	V
I_D	Drain Current - Continuous (T _C = 25°C)		-33.5	Α
	- Continuous (T _C = 100°C)		-23.5	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	-134	Α
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	2200	mJ
I _{AR}	Avalanche Current	(Note 1)	-33.5	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	15.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		-6.0	V/ns
P _D	Power Dissipation (T _A = 25°C) *		3.75	W
_	Power Dissipation (T _C = 25°C)		155	W
	- Derate above 25°C		1.03	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T _L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQB34P10TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.97	
D	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQB34P10TM	FQB34P10	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics

T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Uni
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-100			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, Referenced to 25°C		-0.1		V/°(
Inee		V _{DS} = -100 V, V _{GS} = 0 V			-1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = -80 V, T _C = 150°C			-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-2.0		-4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -16.75 A		0.049	0.06	Ω
9 _{FS}	Forward Transconductance	V _{DS} = -40 V, I _D = -16.75 A		23		S
Dynami	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$		2240	2910	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		730	950	pF
C _{rss}	Reverse Transfer Capacitance			170	220	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = -50 V, I _D = -33.5 A,		25	60	ns
t _r	Turn-On Rise Time	$R_{G} = 25 \Omega$		250	510	ns
t _{d(off)}	Turn-Off Delay Time	- 1.6 =		160	330	ns
t _f	Turn-Off Fall Time	(Note 4)		210	430	ns
Qg	Total Gate Charge	V _{DS} = -80 V, I _D = -33.5 A,		85	110	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V		15		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	/	45		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I _S	Source Diode Characteristics and Maximum Ratings Maximum Continuous Drain-Source Diode Forward Current				-33.5	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				-134	Α
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -33.5 A			-4.0	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = -33.5 A,		160		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		0.88	//	μС

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = mH, I_{AS} = -33.5A, V_{DD} = -25 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} \leq -33.5 A, di/dt \leq 300 A/µs , V_{DD} \leq BV_{DSS}, starting T_J = 25°C.
- ${\bf 4.} \ {\bf Essentially \ independent \ of \ operating \ temperature}.$

Typical Characteristics

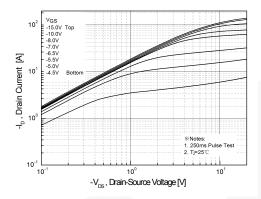


Figure 1. On-Region Characteristics

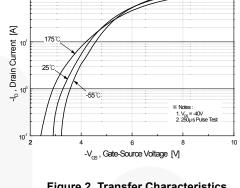


Figure 2. Transfer Characteristics

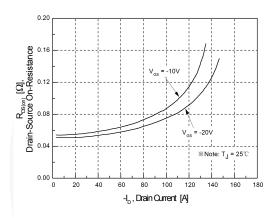


Figure 3. On-Resistance Variation vs. **Drain Current and Gate Voltage**

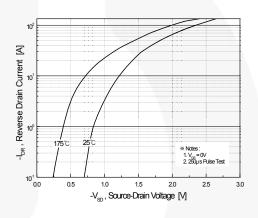


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

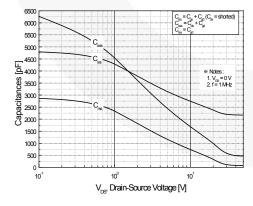


Figure 5. Capacitance Characteristics

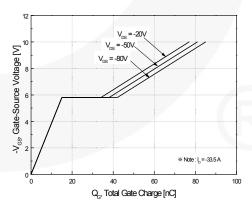


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

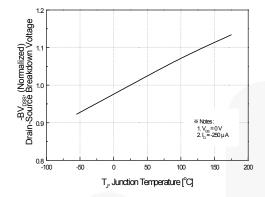


Figure 7. Breakdown Voltage Variation vs. Temperature

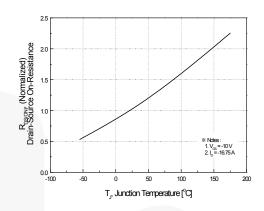


Figure 8. On-Resistance Variation vs. Temperature

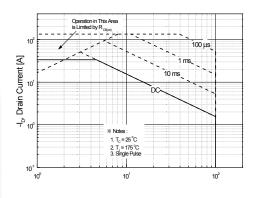


Figure 9. Maximum Safe Operating Area

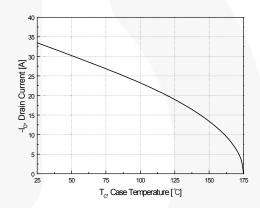


Figure 10. Maximum Drain Current vs. Case Temperature

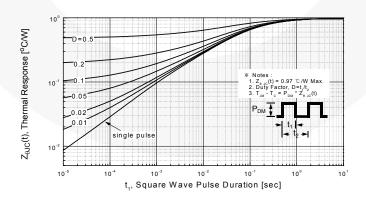


Figure 11. Transient Thermal Response Curve

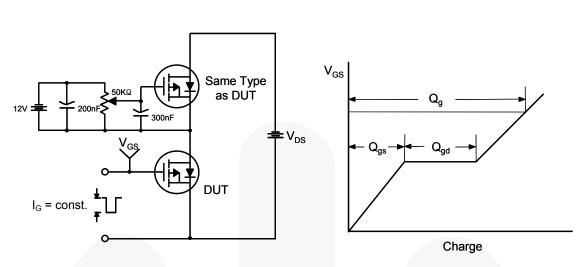


Figure 12. Gate Charge Test Circuit & Waveform

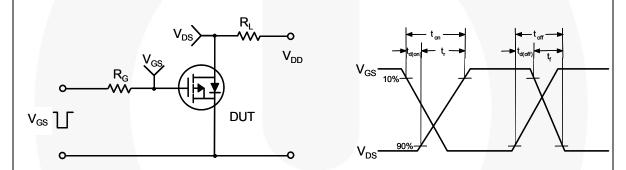


Figure 13. Resistive Switching Test Circuit & Waveforms

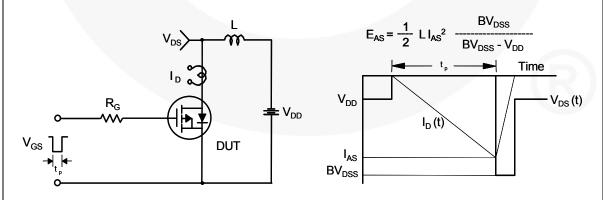
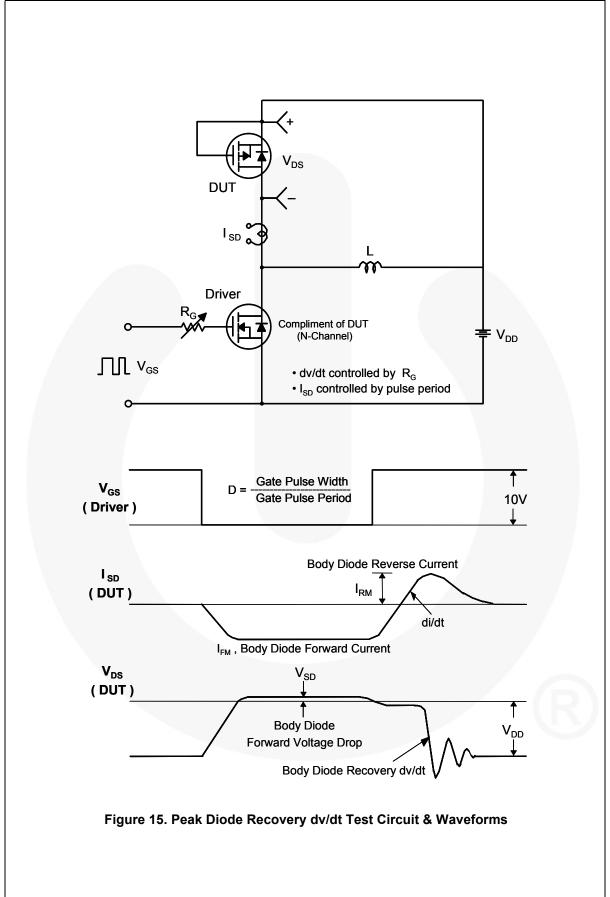
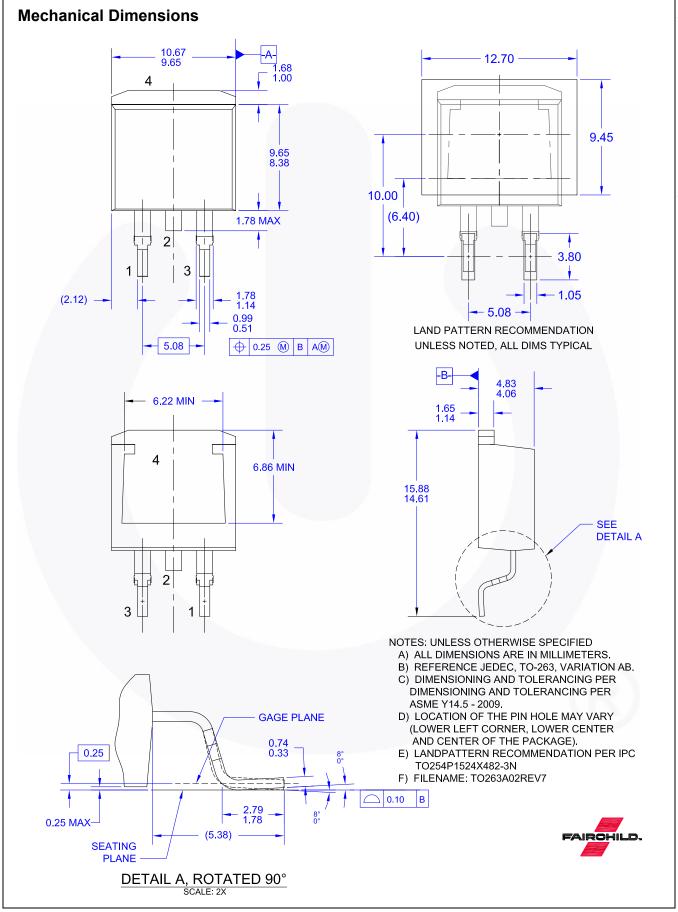


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms









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